# DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1995 Oct 25 2001 Nov 15



# **BGD502**

### FEATURES

- Excellent linearity
- Extremely low noise
- Silicon nitride passivation
- Rugged construction
- TiPtAu metallized crystals ensure optimal reliability.

## DESCRIPTION

Hybrid amplifier modules for CATV systems operating over a frequency range of 40 to 550 MHz at a voltage supply of 24 V (DC).

## **PINNING - SOT115J**

PIN	DESCRIPTION	
1	input	
2, 3	common	
5	+V <sub>B</sub>	
7, 8	common	
9	output	



### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	18	19	dB
		f = 550 MHz	18.8	20.8	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	-	435	mA

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
Vi	RF input voltage		65	dBmV
T <sub>stg</sub>	storage temperature		+100	°C
T <sub>mb</sub>	operating mounting base temperature		+100	°C

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### CHARACTERISTICS

**Table 1** Bandwidth 40 to 550 MHz;  $V_B = 24 \text{ V}$ ;  $T_{mb} = 35 \text{ °C}$ ;  $Z_S = Z_L = 75 \Omega$ .

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	18	_	19	dB
		f = 550 MHz	18.8	-	20.8	dB
SL	slope cable equivalent	f = 40 to 550 MHz	0.2	-	2.2	dB
FL	flatness of frequency response	f = 40 to 550 MHz	_	_	±0.3	dB
s <sub>11</sub>	input return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	_	-	dB
\$ <sub>22</sub>	output return losses	f = 40 to 80 MHz	20	_	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 550 MHz	18	_	-	dB
s <sub>21</sub>	phase response	f = 50 MHz	+135	_	+225	deg
СТВ	composite triple beat	77 channels flat; $V_o = 44 \text{ dBmV}$ ; measured at 547.25 MHz	-	-	-65	dB
X <sub>mod</sub>	cross modulation	77 channels flat; $V_o = 44 \text{ dBmV}$ ; measured at 55.25 MHz	-	-	-68	dB
CSO	composite second order distortion	77 channels flat; $V_o = 44 \text{ dBmV}$ ; measured at 548.5 MHz	-	-	-62	dB
d <sub>2</sub>	second order distortion	note 1	_	-	-72	dB
Vo	output voltage	d <sub>im</sub> = -60 dB; note 2	64	-	-	dBmV
NF	noise figure	f = 550 MHz	_	-	8	dB
I <sub>tot</sub>	total current consumption (DC)	note 3	_	415	435	mA

#### Notes

1. fp = 55.25 MHz; Vp = 44 dBmV; fq = 493.25 MHz; Vq = 44 dBmV; measured at fp + fq = 548.5 MHz.

2. Measured according to DIN45004B: fp = 540.25 MHz; Vp = Vo; fq = 547.25 MHz; Vq = Vo –6 dB; fr = 549.25 MHz; Vr = Vo –6 dB; measured at fp + fq – fr = 538.25 MHz.

3. The module normally operates at VB = 24 V, but are able to withstand supply transients up to VB = 30 V.

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	18	-	19	dB
		f = 450 MHz	18.6	-	20.6	dB
SL	slope cable equivalent	f = 40 to 450 MHz	0.2	-	1.8	dB
FL	flatness of frequency response	f = 40 to 450 MHz	-	-	±0.3	dB
S <sub>11</sub>	input return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
S <sub>22</sub>	output return losses	f = 40 to 80 MHz	20	-	-	dB
		f = 80 to 160 MHz	19	-	-	dB
		f = 160 to 450 MHz	18	-	-	dB
s <sub>21</sub>	phase response	f = 50 MHz	+135	-	+225	deg
СТВ	composite triple beat	60 channels flat; $V_o = 46 \text{ dBmV}$ ; measured at 445.25 MHz	-	-	-67	dB
CSO	composite second order distortion	60 channels flat; $V_o = 46 \text{ dBmV}$ ; measured at 446.5 MHz	-	-	-60	dB
X <sub>mod</sub>	cross modulation	60 channels flat; $V_o = 46 \text{ dBmV};$ measured at 55.25 MHz	-	-	-67	dB
d <sub>2</sub>	second order distortion	note 1	-	-	-75	dB
Vo	output voltage	d <sub>im</sub> = -60 dB; note 2	67	-	-	dBmV
NF	noise figure	f = 450 MHz	_	-	7	dB
l <sub>tot</sub>	total current consumption (DC)	note 3	_	415	435	mA

## $\label{eq:table 2} \mbox{Table 2} \mbox{ Bandwidth 40 to 450 MHz; } V_B = 24 \mbox{ V; } T_{mb} = 35 \mbox{ }^\circ\mbox{C} ; \mbox{ } Z_S = Z_L = 75 \mbox{ } \Omega.$

#### Notes

1. fp = 55.25 MHz; Vp = 46 dBmV; fq = 391.25 MHz; Vq = 46 dBmV; measured at fp + fq = 446.5 MHz.

- 2. Measured according to DIN45004B: fp = 440.25 MHz; Vp = Vo; fq = 447.25 MHz; Vq = Vo -6 dB; fr = 449.25 MHz; Vr = Vo -6 dB; measured at fp + fq fr = 438.25 MHz.
- 3. The modules normally operate at VB = 24 V, but are able to withstand supply transients up to VB = 30 V.

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;

### PACKAGE OUTLINE



**BGD502** 

SOT115J

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#### DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

**BGD502** 

# 550 MHz, 18.5 dB gain power doubler amplifier

NOTES

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#### **Contact information**

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